

**isc Silicon NPN Power Transistor**

**2SC3729**

**DESCRIPTION**

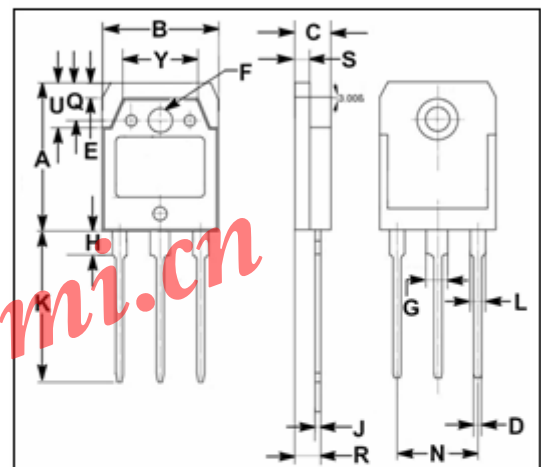
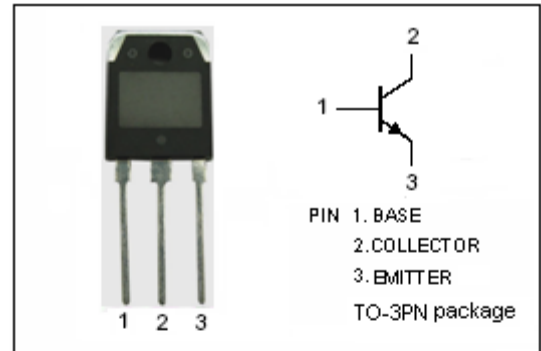
- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 800V(\text{Min})$
- Wide Area of Safe Operation

**APPLICATIONS**

- Designed for TV horizontal deflection output applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base voltage	6	V
$I_C$	Collector Current-Continuous	5	A
$I_{CM}$	Collector Current-Peak	16	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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**ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = ∞	800			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1.25A			2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1.25A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			0.5	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		8		

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